



DSS8110Y

100V LOW V_{CE(sat)} NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (DSS9110Y)
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green Device" (Note 2)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

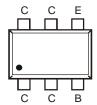








Device Symbol



Pin-Out Top

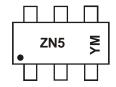
Ordering Information (Note 3)

ſ	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	DSS8110Y-7	ZN5	7	8mm	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZN5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	20	10	20	11	20	12	20	13	20	14	20	15
Code		<	`	Y	- 2	7	-	4	Е	3	(2
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = 25°C unless otherwise specified

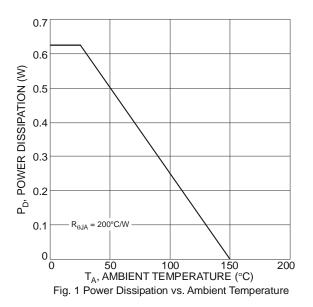
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	Ic	1	Α
Peak Pulse Collector Current	I _{CM}	3	Α
Base Current – Continuous	I _B	0.3	А

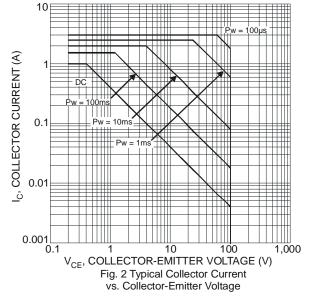
Thermal Characteristics

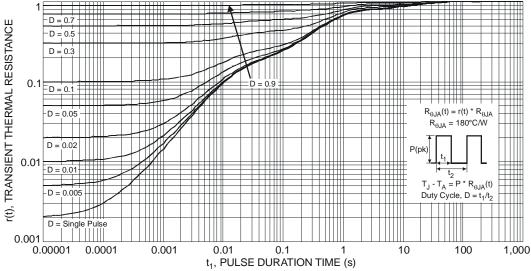
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P _D	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ hetaJA}$	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

4. Device mounted on FR-4 PCB, with minimum recommended pad layout.





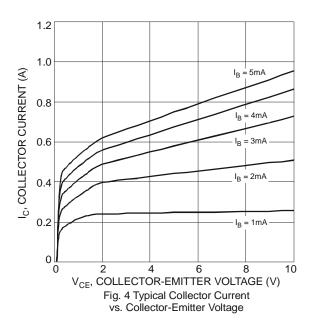


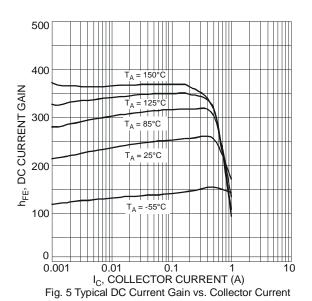


Electrical Characteristics @TA = 25°C unless otherwise specified

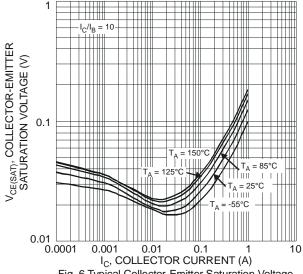
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	-					
Collector-Base Breakdown Voltage	BV _{CBO}	120			V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	100			V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	_		V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	$V_{CB} = 80V, I_E = 0$
Concetor Caton Current	ICBO	_	_	50	μΑ	$V_{CB} = 80V, I_{E} = 0, T_{A} = 150^{\circ}C$
Collector Cutoff Current	I _{CES}	_	_	100	nA	$V_{CE} = 80V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)						
	h _{FE}	150	_	_	V	$V_{CE} = 10V$, $I_C = 1mA$
DC Current Gain		150	_	500		$V_{CE} = 10V, I_{C} = 250mA$
Do Garrett Garr		100	_	_		$V_{CE} = 10V, I_{C} = 500mA$
		80	_	_		$V_{CE} = 10V, I_{C} = 1A$
		_	_	40		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	120	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	_	200		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	_	200	mΩ	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	1		1.05	V	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn On Voltage	V _{BE(on)}			0.9	V	$V_{CE} = 10V, I_{C} = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	_	7.5	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f _T	100	_	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz

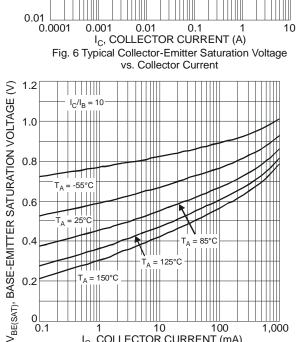
Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.





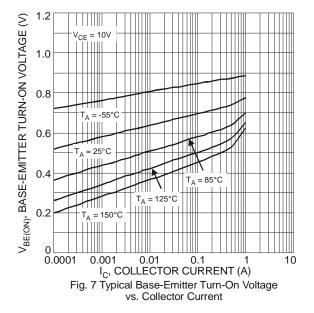






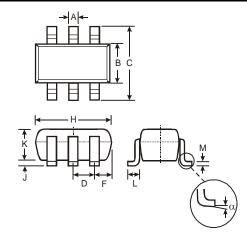
1 10 100 I_C, COLLECTOR CURRENT (mA) Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current

1,000



Package Outline Dimensions

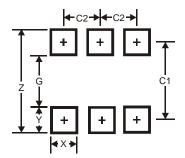
0.1



	SOT-363						
Dim	Min	Max					
Α	0.10	0.30					
В	1.15	1.35					
С	2.00	2.20					
D	0.65	Тур					
F	0.40	0.45					
Н	1.80	2.20					
J	0	0.10					
K	0.90	1.00					
L	0.25	0.40					
М	0.10	0.22					
α	0°	8°					
All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

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